

## Supporting Information

### Highly Stabilized Silicon Nanoparticles for Lithium Storage *via* Hierarchical Carbon Architecture

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**Figure S1.** The morphological evolution of N-doped CNTs/Si@C.

**Figure S2.** (a) TEM image and (b-d) corresponding elemental mappings of Si@ZnO.

**Figure S3.** (a) SEM and (b) TEM images of Si@ZIF-67.

**Figure S4.** (a) SEM and (b) TEM images of Si@ZIF-67@PDA.

**Figure S5.** Nitrogen adsorption-desorption isotherm and pore size distribution (inset) of (a) Si@ZIF-67 and (b) Si@ZIF-67@PDA.

**Figure S6.** XRD patterns of Si@ZIF-67 and Si@ZIF-67@PDA.

**Figure S7.** (a-c) High-resolution XPS spectra of Si 2p, C 1s and Co 2p of N-doped CNTs/Si@C.

**Figure S8.** Capacitive contributions to charge storage of N-doped CNTs/Si@C at a scan rate of (a)  $0.3 \text{ mV s}^{-1}$ , (b)  $0.5 \text{ mV s}^{-1}$ , (c)  $0.8 \text{ mV s}^{-1}$ , and (d)  $1 \text{ mV s}^{-1}$ .

**Figure S9.** Voltage profiles of the N-doped CNTs/Si@C electrode for different cycles at a current densities of  $500 \text{ mA g}^{-1}$ .

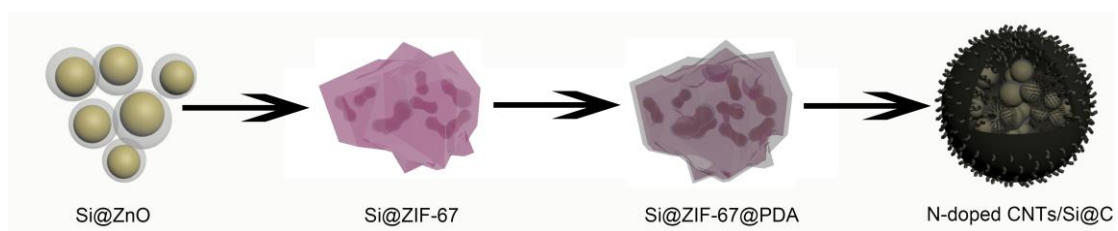
**Figure S10.** Voltage profiles of the N-doped CNTs/Si@C electrode for different cycles at a current densities of  $1000 \text{ mA g}^{-1}$ .

**Figure S11.** Voltage profiles of the N-doped CNTs/Si@C electrode for different cycles at a current densities of  $2000 \text{ mA g}^{-1}$ .

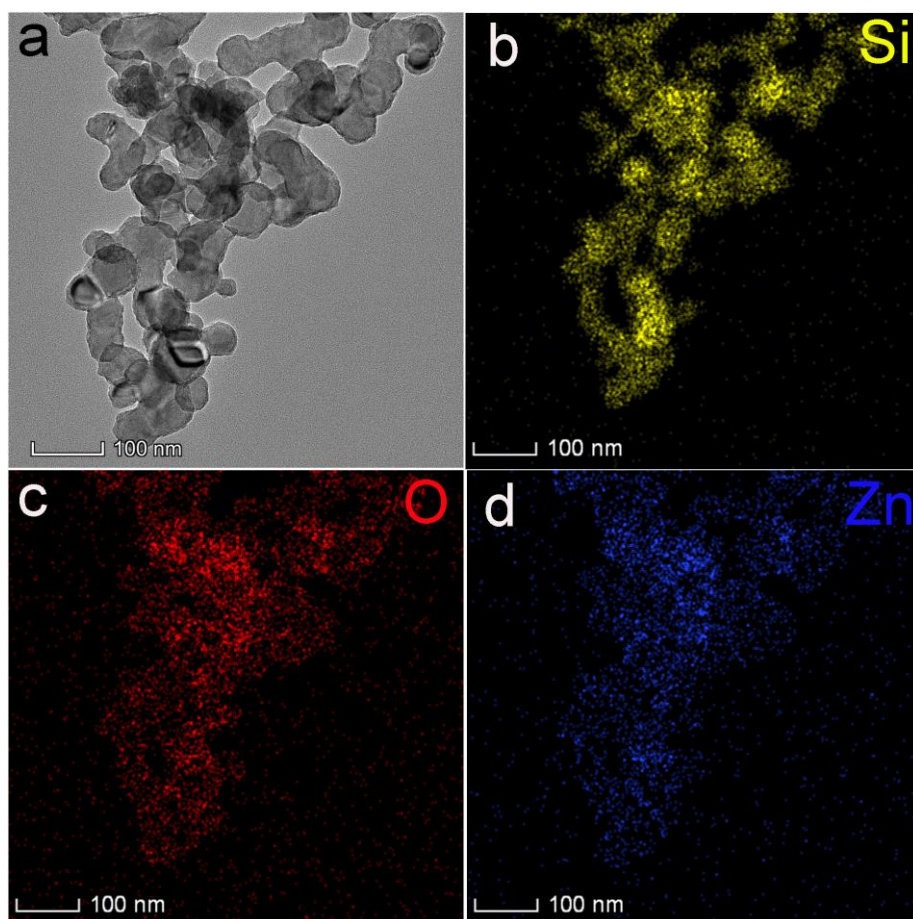
**Figure S12.** Voltage profiles of N-doped CNTs/Si@C electrode under various current densities.

**Figure S13.** Rate capability of N-doped CNTs/Si@C electrode.

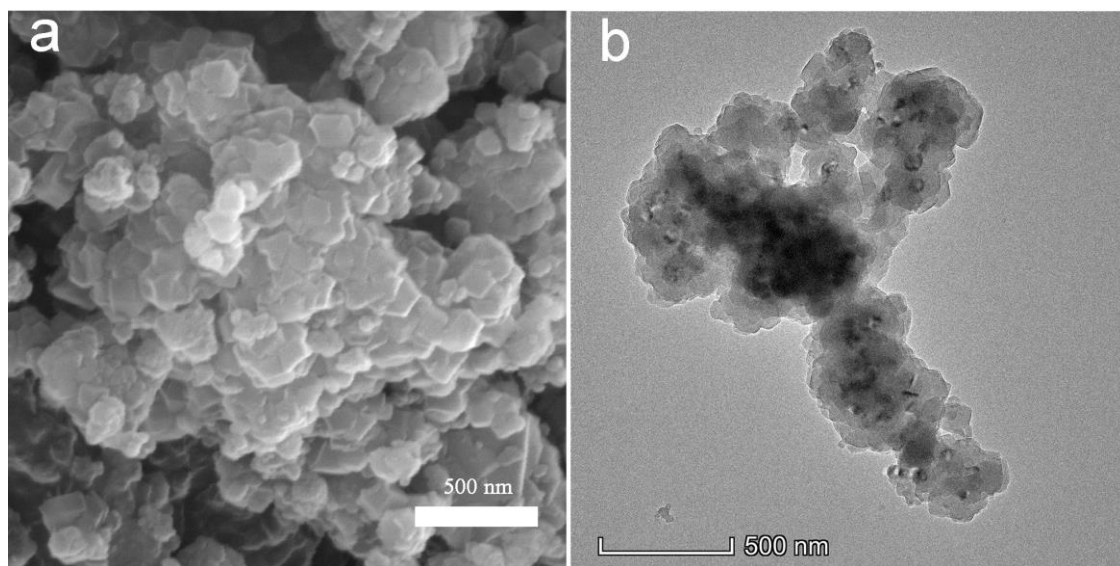
**Figure S14.** (a) The cycling performance of NCA half cell at 1 C rate (1 C= $170 \text{ mA g}^{-1}$ ) and (b) corresponding charge-discharge profiles.



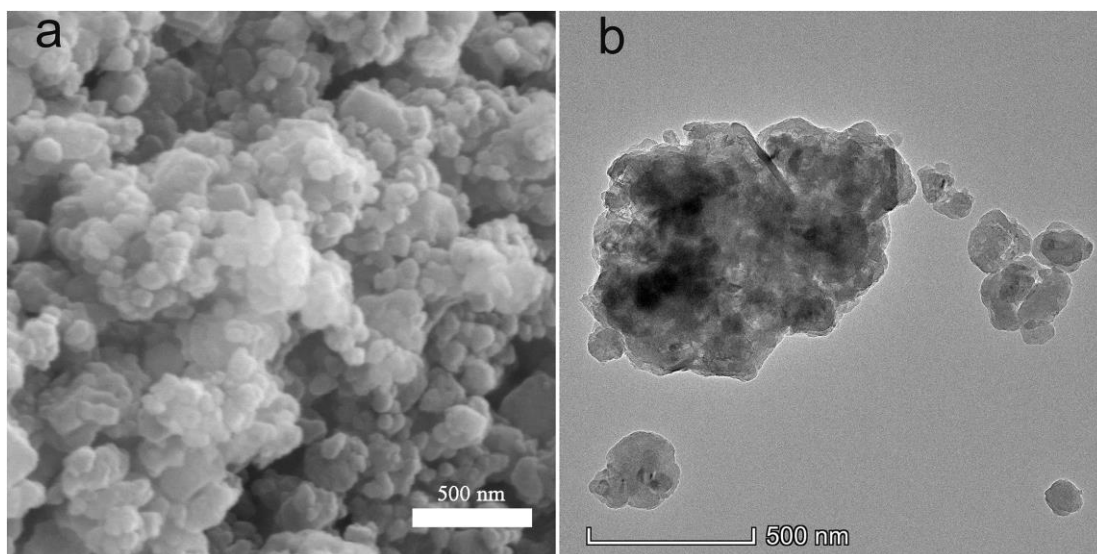
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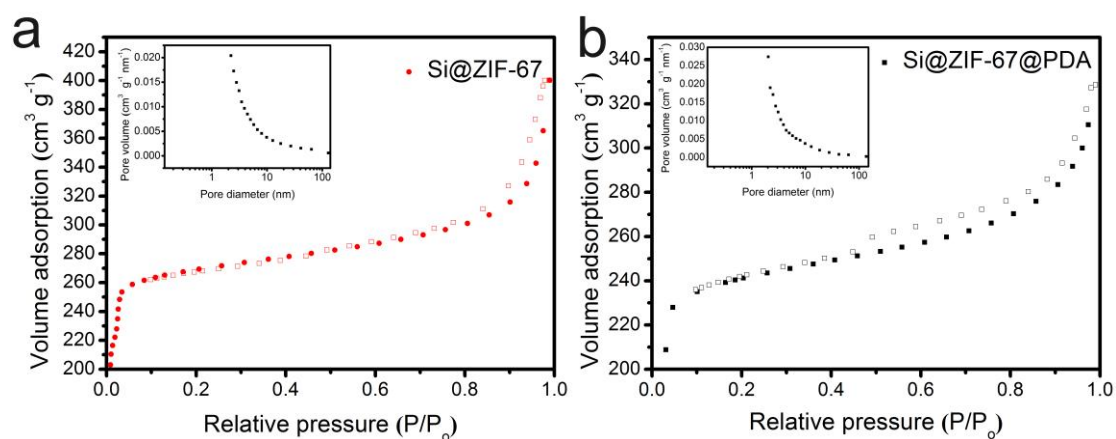
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**Figure S3.** (a) SEM and (b) TEM images of Si@ZIF-67.

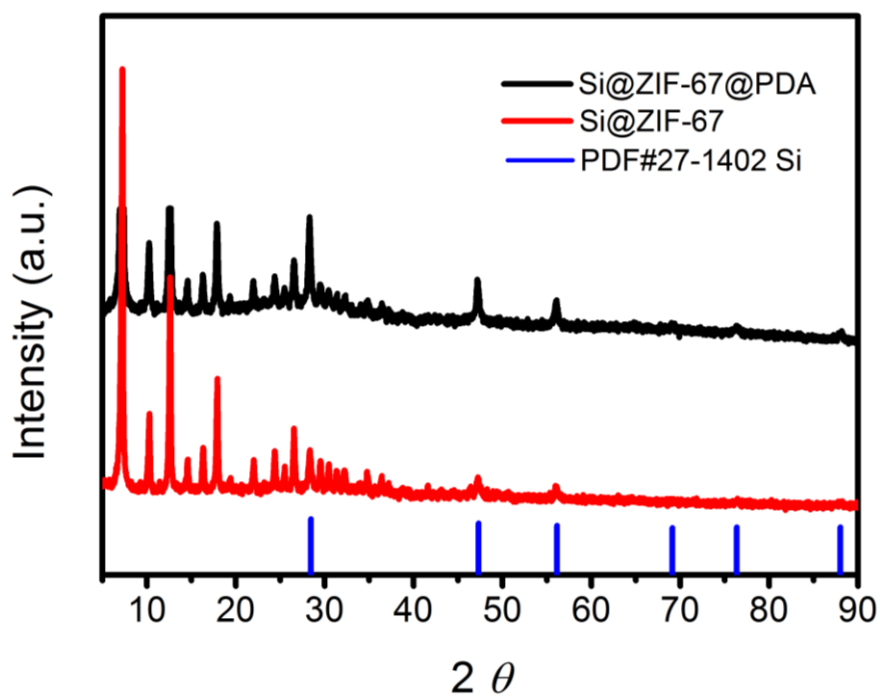


**Figure S4.** (a) SEM and (b) TEM images of Si@ZIF-67@PDA.



**Figure S5.** Nitrogen adsorption-desorption isotherm and pore size distribution (inset) of (a) Si@ZIF-67 and (b) Si@ZIF-67@PDA.

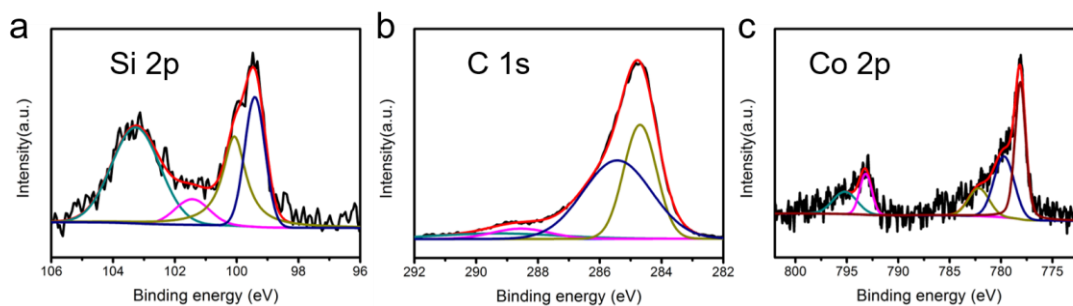
S.No	Sample Name	Surface Area (m <sup>2</sup> g <sup>-1</sup> )	Pore Size (nm)
1.	Si@ZIF-67	898	1 -3
2.	Si@ZIF-67@PDA	821	3 - 10
3.	N-doped CNTs/Si@C	234	20 - 30



**Figure S6.** XRD patterns of Si@ZIF-67 and Si@ZIF-67@PDA.

In Figure S6, all diffraction peaks of Si@ZIF-67 match well with both Si phase (JPCDS No. 27-1402) and ZIF-67 phase. There is no obvious change in the XRD pattern of Si@ZIF-67@PDA sample, indicating that the introduction of PDA does not change the crystal structure of the components in Si@ZIF-67 materials.



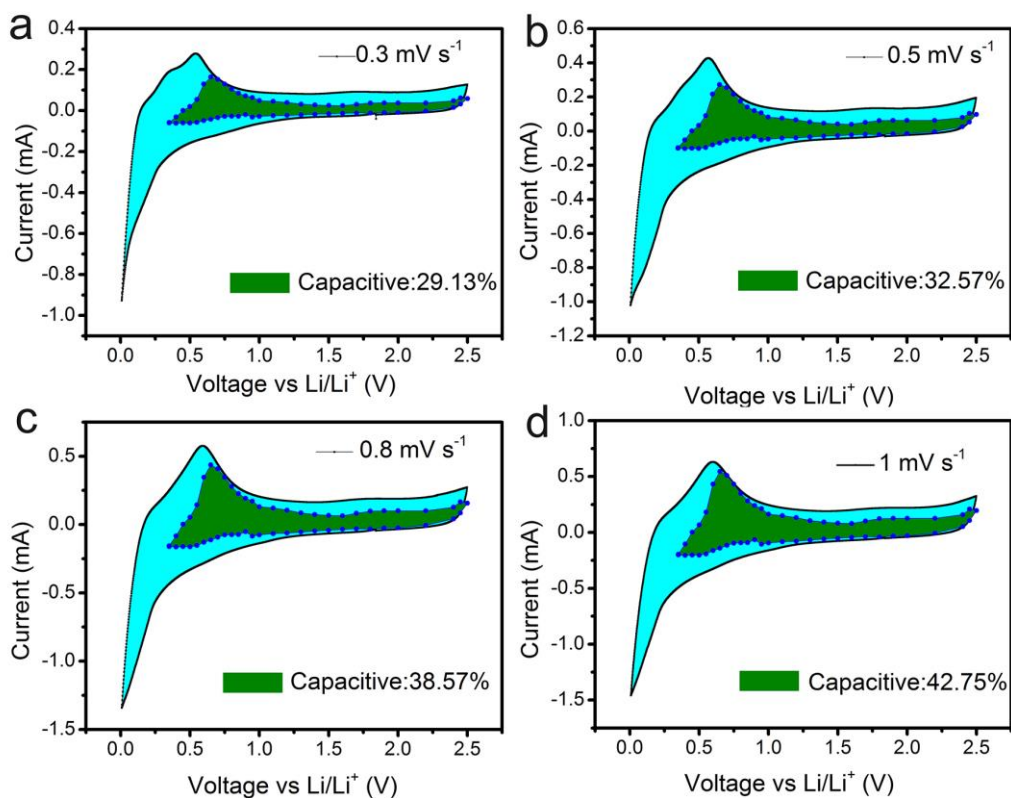


**Figure S7.** (a-c) High-resolution XPS spectra of Si 2p, C 1s and Co 2p of N-doped CNTs/Si@C.

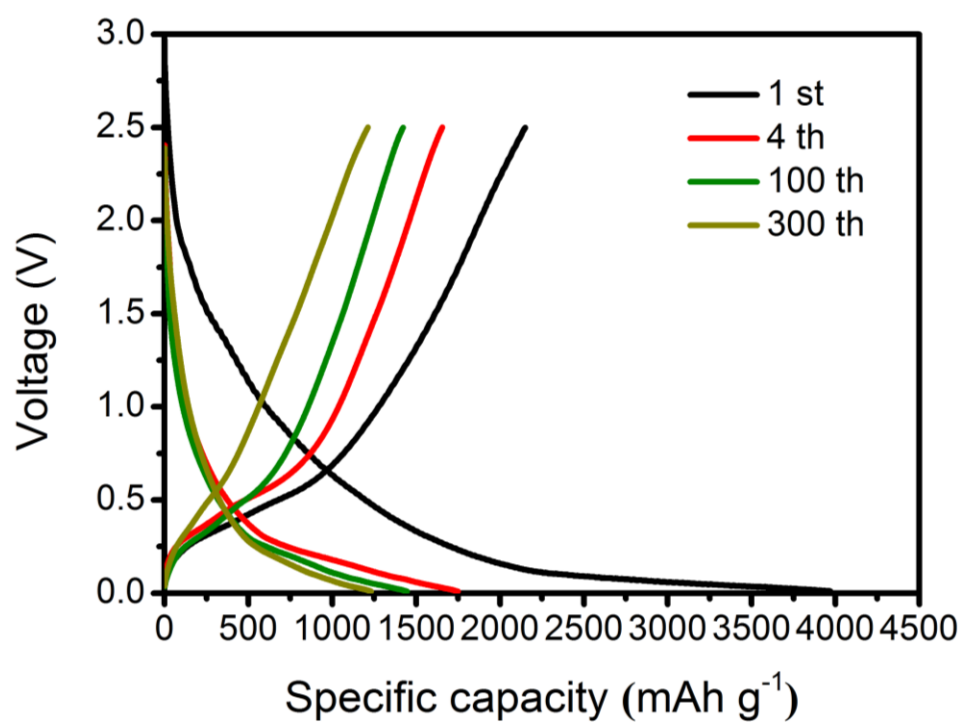
The Si2p peaks observed around at 103.5 eV and 99.6 eV are assigned to the presence of SiO<sub>x</sub> on the Si surface and unoxidized Si atoms, while a weak peak at 101.8 eV belongs to Si-C are observed.<sup>1</sup> 100.3 eV is attributable to SiO<sub>x</sub>.<sup>2</sup>

The high-resolution C1s spectrum consists of four peaks centered at 284.7, 286.8, 288.7, and 289.2 eV, corresponding to C-C/C=C, C-OH, C=O/C-N, and -COOH, respectively.<sup>3</sup>

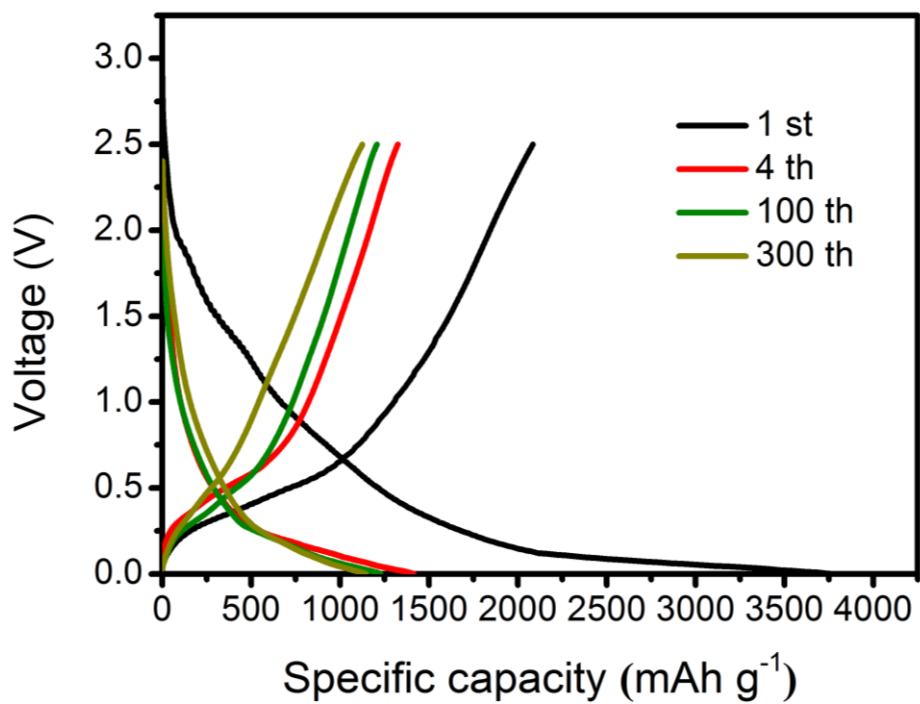
In the high resolution spectrum of Co, the peaks at about 793 eV and 795 eV correspond to Co 2p<sub>1/2</sub>, and the peaks at about 778.2 eV 780eV, and 795 eV correspond to Co 2p<sub>3/2</sub>.<sup>4</sup>



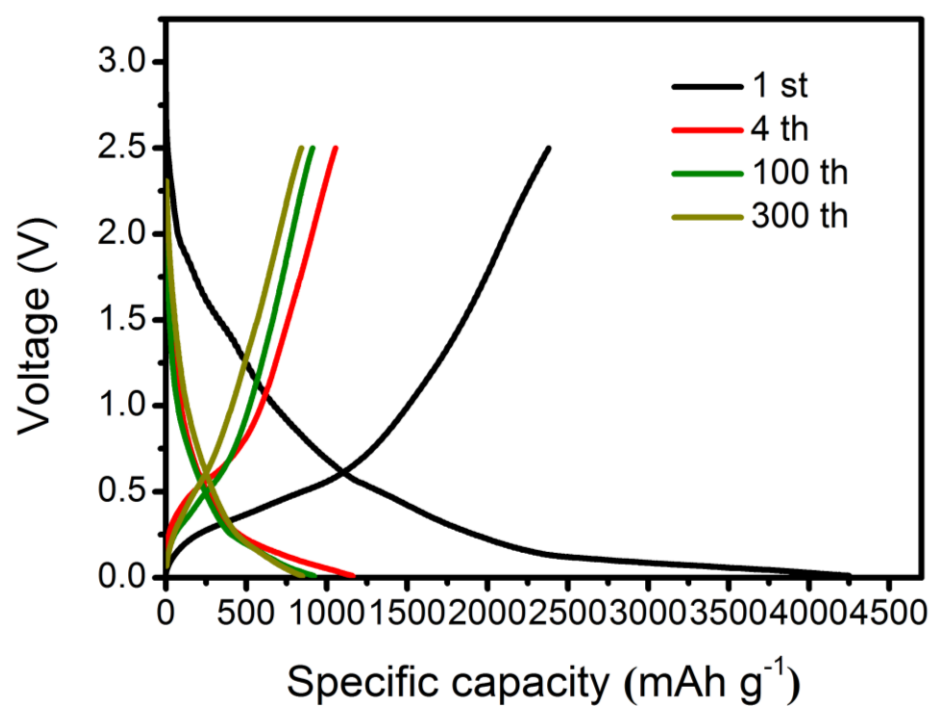
**Figure S8.** Capacitive contributions to charge storage of N-doped CNTs/Si@C at a scan rate of (a) 0.3 mV s<sup>-1</sup>, (b) 0.5 mV s<sup>-1</sup>, (c) 0.8 mV s<sup>-1</sup>, and (d) 1 mV s<sup>-1</sup>.



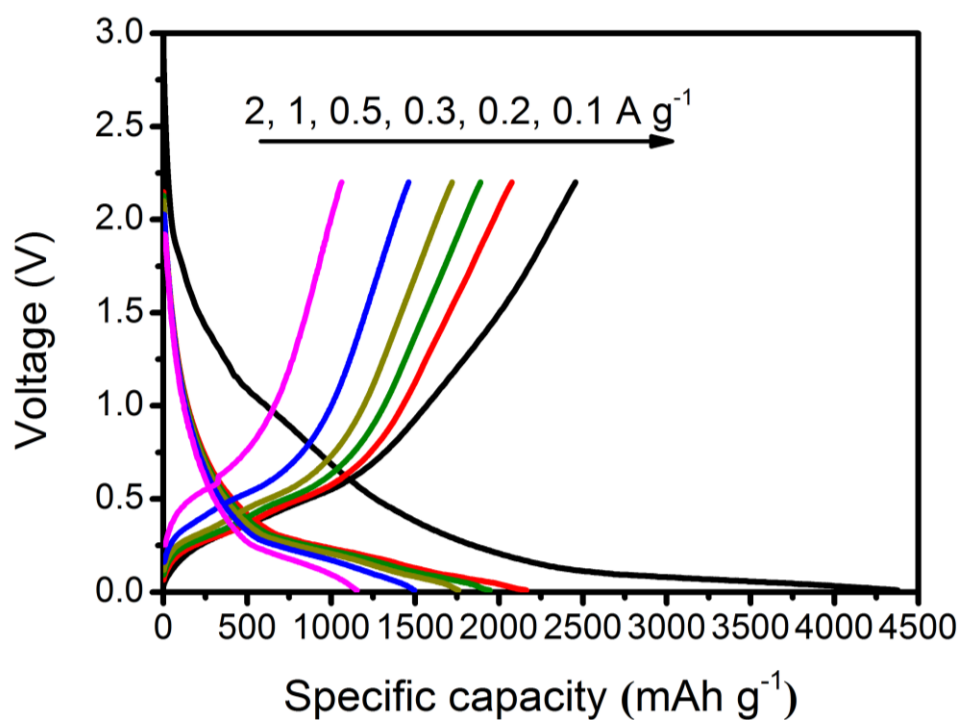
**Figure S9.** Voltage profiles of the N-doped CNTs/Si@C electrode for different cycles at a current densities of 500 mA g<sup>-1</sup>.



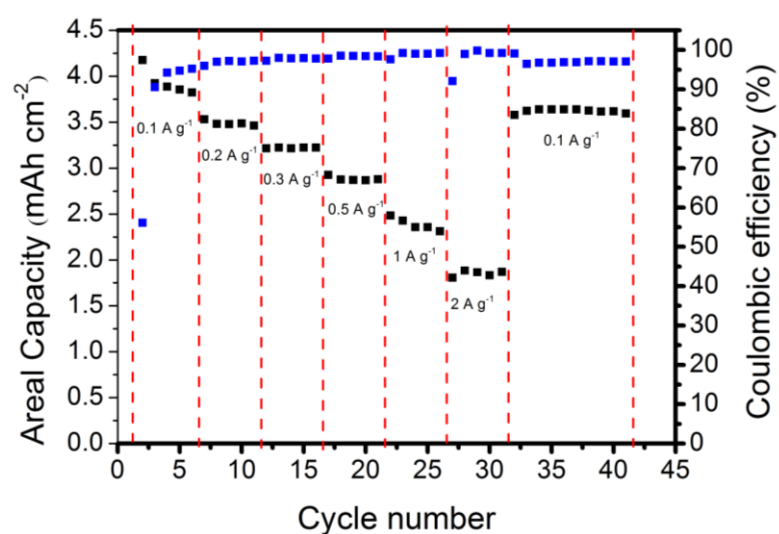
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**Figure S11.** Voltage profiles of the N-doped CNTs/Si@C electrode for different cycles at a current densities of 2000 mA g<sup>-1</sup>.

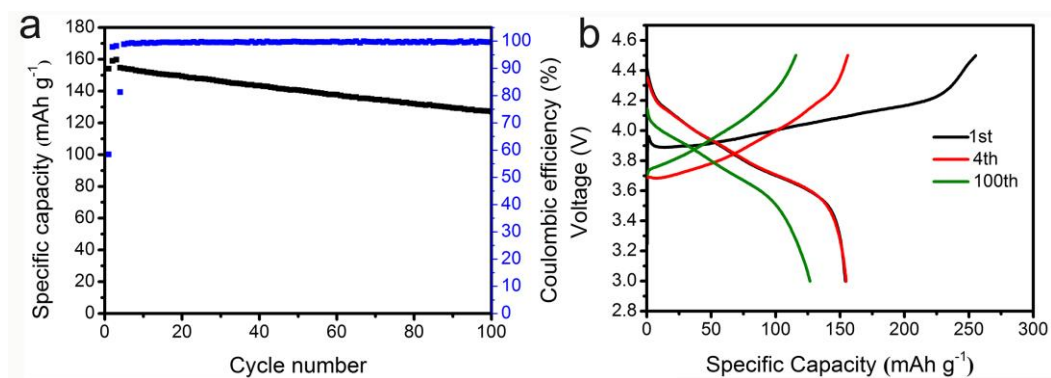


**Figure S12.** Voltage profiles of N-doped CNTs/Si@C electrode under various current densities.



**Figure S13.** Rate capability of N-doped CNTs/Si@C electrode.

As shown in and Figure S13, the N-doped CNTs/Si@C electrode also shows an excellent rate capability showed a higher areal capacity of about 4.17 mAh cm<sup>-2</sup>, 3.52 mAh cm<sup>-2</sup>, 3.21 mAh cm<sup>-2</sup>, 2.92 mAh cm<sup>-2</sup>, 2.48 mAh cm<sup>-2</sup>, and 1.88 mAh cm<sup>-2</sup> at 0.1 A g<sup>-1</sup>, 0.2 A g<sup>-1</sup>, 0.3 A g<sup>-1</sup>, 0.5 A g<sup>-1</sup>, 1 A g<sup>-1</sup>, and 2 A g<sup>-1</sup>, respectively.



**Figure S14.** (a) The cycling performance of NCA half cell at 1 C rate (1 C=170 mA g<sup>-1</sup>) and (b) corresponding charge-discharge profiles.



## References

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